# Abstracts

## A 3.4 V, 1 watt cellular DAMPS GaAs MESFET power amplifier with 50% efficiency

*S.S. Taylor. "A 3.4 V, 1 watt cellular DAMPS GaAs MESFET power amplifier with 50% efficiency." 1998 Radio Frequency Integrated Circuits (RFIC) Symposium 98. (1998 [RFIC]): 73-76.*

A 3.4 V, 1 W cellular DAMPS power amplifier with 50% efficiency has been implemented and tested. The single-supply PA incorporates biasing, PMOS interface, and negative supply voltage generation on-chip, and is assembled in a TSSOP20 package with a downset paddle. The circuit achieves 30 dB of power gain, a 12 dB input return loss, and is implemented in a 20 GHz ion-implanted GaAs MESFET manufacturing process.

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